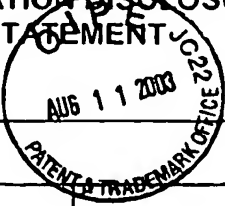


INFORMATION DISCLOSURE STATEMENT 		Atty Docket: 02RO18854478 Serial No.: 10/616,413 Applicant: MIRABEL ET AL. Filing Date: July 9, 2003 Group:					
U.S. PATENT DOCUMENTS							
Examiner Initials		Document Number	Date	Name	Class	Sub Class	Filing Date
VTN	AA	5,726,933	3/10/98	Lee et al.	365	185.18	
	AB	5,781,477	7/14/98	Rinerson et al.	365	185.29	
	AC	5,790,460	8/4/98	Chen et al.	365	185.29	
	AD	5,933,367	8/3/99	Matsuo et al.	365	185.29	
VTN	AE	6,236,596	5/22/01	Sobek et al.	365	185.27	
	AF						
	AG						
	AH						
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Sub Class	Translation
	AI						
	AJ						
	AK						
	AL						
OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)							
VTN	AM	Laffont et al., <i>Decreasing EEPROM Programming Bias with Negative Voltage Reliability Impact</i> , IEEE International Workshop on Memory Technology, Design and Testing (MTDT 2002), July 10, 2002, Pages 168-173, XP010601068					
VTN	AN	Benzerti et al., <i>Effect of the Selection MOS Transistor Polarization Voltage During a Write and an Erase Operation of an EEPROM Memory Cell</i> , Microelectronics, 1998, ICM 98, Proceedings of the Tenth International Conference on Monastir, Tunisia, December 14-16, 1998, Piscataway, NJ, US, December 14, 1998, Pages 149-152, XP010371938					
	AO						
EXAMINER: <i>W. H. N. G.</i>				DATE CONSIDERED: 8/4/04			

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.